AMENDMENTS TO THE CLAIMS

Claims 1-5 (canceled).

6. (original) A method for forming a memory device, comprising:

forming a gate dielectric on a semiconductor substrate;

forming source and drain regions on opposite sides of said gate dielectric;

forming a floating gate on said gate dielectric;

forming a silicon-doped Al₂O₃ layer by chemical vapor deposition on said floating gate; and

forming a control gate on said doped Al₂O₃ layer.

- 7. (original) The method of claim 6, wherein said step of forming said silicondoped Al_2O_3 layer is performed at an energy of approximately 10 keV and at a dose of approximately $1 \times 10^{14} / \text{cm}^2$ to $1 \times 10^{15} / \text{cm}^2$.
- 8. (original) The method of claim 6 further comprising forming a silicide layer on top of said control gate.
- 9. (original) The method of claim 6, wherein said gate dielectric is formed of a material selected from the group consisting of oxynitride and oxide.
- 10. (original) The method of claim 6, wherein said memory device is a flash memory device.

Claims 11-26 (canceled).